



**1N60
1N60P**

Features

- High Reliability
- Low Reverse Current and Low Forward Voltage
- Marking : Cathode band and type number
- Moisture Sensitivity: Level 1 per J-STD-020C

**Schottky Barrier
Rectifier**

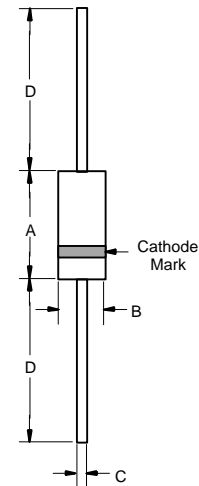
Maximum Ratings

- Storage & Operating Junction Temperature: -65°C to +125°C

DO-35

Electrical Characteristics @ 25°C Unless Otherwise Specified

Parameter	Symbol	Type	Value	Test Condition
Repetitive Peak Reverse Voltage	V_{RRM}	1N60	40V	
		1N60P	45V	
Average Forward Current	$I_{F(AV)}$	1N60	30mA	$T_a = 25^\circ\text{C}$
		1N60P	50mA	$T_a = 25^\circ\text{C}$
Peak Forward Surge Current	I_{FSM}	1N60	150mA	$t_p \leq 1\text{s}$
		1N60P	500mA	$t_p \leq 1\text{s}$
Junction Ambient	R_{thJA}		250K/W	On PC board 50mm × 50mm × 1.6mm



Note: 1. Lead in Glass Exemption Applied, see EU Directive Annex 5.

DIMENSIONS

DIM	INCHES		MM		NOTE
	MIN	MAX	MIN	MAX	
A	---	.166	---	4.2	
B	---	.079	---	2.00	
C	---	.020	---	.52	
D	1.000	---	25.40	---	

1N60, 1N60P

Electrical Characteristics @ 25°C Unless Otherwise Specified

Parameter	Test Conditions	Type	Symbol	Min	Typ	Max	Unit
Forward voltage	$I_F=1\text{mA}$	1N60	V_F	---	0.32	0.5	V
		1N60P	V_F	---	0.24	0.5	V
	$I_F=30\text{mA}$	1N60	V_F	---	0.65	1.0	V
		1N60P	V_F	---	0.65	1.0	V
Reverse current	$V_R=15\text{V}$	1N60	I_R	---	0.1	0.5	μA
		1N60P	I_R	---	0.5	1.0	μA
Junction capacitance	$V_R=1\text{V}, f=1\text{MHz}$	1N60	C_J	---	2.0	---	pF
	$V_R=10\text{V}, f=1\text{MHz}$	1N60P	C_J	---	6.0	---	pF
Reverse recovery time	$I_F=I_R=1\text{mA}, I_{rr}=1\text{mA}$ $R_C=100\Omega$		t_{rr}	---	---	1.0	ns
